Chen Pan

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/9150818/publications.pdf

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22	2,375	516710 16	642732 23
papers	citations	h-index	g-index

24	24	24	3781
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Robust memristors based on layered two-dimensional materials. Nature Electronics, 2018, 1, 130-136.	26.0	539
2	Room temperature high-detectivity mid-infrared photodetectors based on black arsenic phosphorus. Science Advances, 2017, 3, e1700589.	10.3	419
3	Van der Waals epitaxial growth and optoelectronics of large-scale WSe2/SnS2 vertical bilayer pâ€“n junctions. Nature Communications, 2017, 8, 1906.	12.8	369
4	Gate-tunable van der Waals heterostructure for reconfigurable neural network vision sensor. Science Advances, 2020, 6, eaba6173.	10.3	202
5	Reconfigurable logic and neuromorphic circuits based on electrically tunable two-dimensional homojunctions. Nature Electronics, 2020, 3, 383-390.	26.0	191
6	Negative Photoconductance in van der Waals Heterostructure-Based Floating Gate Phototransistor. ACS Nano, 2018, 12, 9513-9520.	14.6	124
7	Gate-Induced Interfacial Superconductivity in 1T-SnSe₂. Nano Letters, 2018, 18, 1410-1415.	9.1	81
8	Networking retinomorphic sensor with memristive crossbar for brain-inspired visual perception. National Science Review, 2021, 8, nwaa172.	9.5	77
9	Experimental Identification of Critical Condition for Drastically Enhancing Thermoelectric Power Factor of Two-Dimensional Layered Materials. Nano Letters, 2018, 18, 7538-7545.	9.1	72
10	Scalable massively parallel computing using continuous-time data representation in nanoscale crossbar array. Nature Nanotechnology, 2021, 16, 1079-1085.	31.5	53
11	Vertical WS2/SnS2 van der Waals Heterostructure for Tunneling Transistors. Scientific Reports, 2018, 8, 17755.	3.3	40
12	Nonvolatile van der Waals Heterostructure Phototransistor for Encrypted Optoelectronic Logic Circuit. ACS Nano, 2022, 16, 4528-4535.	14.6	34
13	Gated tuned superconductivity and phonon softening in monolayer and bilayer MoS2. Npj Quantum Materials, 2017, 2, .	5.2	33
14	Intrinsic p-type W-based transition metal dichalcogenide by substitutional Ta-doping. Applied Physics Letters, 2017, 111, .	3.3	26
15	Analog Circuit Applications Based on Ambipolar Graphene/MoTe₂ Vertical Transistors. Advanced Electronic Materials, 2018, 4, 1700662.	5.1	26
16	Gate-tunable weak antilocalization in a few-layer InSe. Physical Review B, 2018, 98, .	3.2	24
17	Sâ€Type Negative Differential Resistance in Semiconducting Transitionâ€Metal Dichalcogenides. Advanced Electronic Materials, 2019, 5, 1800853.	5.1	17
18	A Braitenberg Vehicle Based on Memristive Neuromorphic Circuits. Advanced Intelligent Systems, 2020, 2, 1900103.	6.1	16

#	Article	IF	Citations
19	Temperature-sensitive spatial distribution of defects in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Pd</mml:mi><mml:msub><mml:mi>Se</mml:mi><mml:mn> flakes. Physical Review Materials, 2021, 5, .	2.4	11
20	Reconfigurable vertical field-effect transistor based on graphene/MoTe2/graphite heterostructure. Science China Information Sciences, 2020, 63, 1.	4.3	6
21	Chemical vapor deposition synthesis of two-dimensional freestanding transition metal oxychloride for electronic applications. Science China Information Sciences, 2019, 62, 1.	4.3	5
22	Vertical Transistors: Analog Circuit Applications Based on Ambipolar Graphene/MoTe₂ Vertical Transistors (Adv. Electron. Mater. 3/2018). Advanced Electronic Materials, 2018, 4, 1870015.	5.1	0